

BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G, SBC847BPDW1T1G Series, BC848CPDW1T1G



ON Semiconductor®

<http://onsemi.com>



SOT-363
CASE 419B
STYLE 1

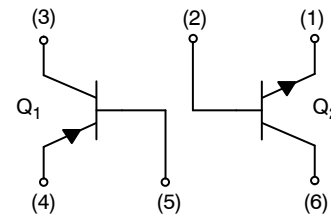
Dual General Purpose Transistors

NPN/PNP Duals (Complementary)

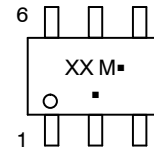
These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*



MARKING DIAGRAM



XX = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

MAXIMUM RATINGS – NPN

| Rating | Symbol | Value | Unit |
|--|-----------|----------------|------|
| Collector-Emitter Voltage BC846, SBC846 BC847, SBC847 BC848 | V_{CEO} | 65 45 30 | V |
| Collector-Base Voltage BC846, SBC846 BC847, SBC847 BC848 | V_{CBO} | 80 50 30 | V |
| Emitter-Base Voltage | V_{EBO} | 6.0 | V |
| Collector Current – Continuous | I_C | 100 | mAdc |

MAXIMUM RATINGS – PNP

| Rating | Symbol | Value | Unit |
|--|-----------|-------------------|------|
| Collector-Emitter Voltage BC846, SBC846 BC847, SBC847 BC848 | V_{CEO} | -65 -45 -30 | V |
| Collector-Base Voltage BC846, SBC846 BC847, SBC847 BC848 | V_{CBO} | -80 -50 -30 | V |
| Emitter-Base Voltage | V_{EBO} | -5.0 | V |
| Collector Current – Continuous | I_C | -100 | mAdc |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ORDERING INFORMATION

| Device | Mark | Package | Shipping† |
|----------------|------|----------------------|------------------------|
| BC846BPDW1T1G | BB | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC846BPDW1T1G | BB | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC846BPDW1T2G | BB | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC847BPDW1T1G | BF | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC847BPDW1T1G | BF | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC847BPDW1T2G | BF | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC848CPDW1T1G | BL | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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SBC847BPDW1T1G Series, BC848CPDW1T1G**

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|-------------------|--|
| Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 380 250 3.0 | mW mW/ $^\circ\text{C}$ mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 328 | $^\circ\text{C/W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

1. FR-5 = 1.0 x 0.75 x 0.062 in.

ELECTRICAL CHARACTERISTICS (NPN) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|--|---------------|-------------------|-------------|-------------|---------------------|
| Collector - Emitter Breakdown Voltage ($I_C = 10\text{ mA}$) BC846, SBC846 Series BC847, SBC847 Series BC848 Series | $V_{(BR)CEO}$ | 65 45 30 | - - - | - - - | V |
| Collector - Emitter Breakdown Voltage ($I_C = 10\ \mu\text{A}, V_{EB} = 0$) BC846, SBC846 Series BC847B, SBC847B Only BC848 Series | $V_{(BR)CES}$ | 80 50 30 | - - - | - - - | V |
| Collector - Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$) BC846, SBC846 Series BC847, SBC847 Series BC848 Series | $V_{(BR)CBO}$ | 80 50 30 | - - - | - - - | V |
| Emitter - Base Breakdown Voltage ($I_E = 1.0\ \mu\text{A}$) BC846, SBC846 Series BC847, SBC847 Series BC848 Series | $V_{(BR)EBO}$ | 6.0 6.0 5.0 | - - - | - - - | V |
| Collector Cutoff Current ($V_{CB} = 30\text{ V}$) ($V_{CB} = 30\text{ V}, T_A = 150^\circ\text{C}$) | I_{CBO} | - - | - - | 15 5.0 | nA μA |

ON CHARACTERISTICS

| | | | | | |
|---|---------------|----------------------|--------------------------|----------------------|----|
| DC Current Gain ($I_C = 10\ \mu\text{A}, V_{CE} = 5.0\text{ V}$) BC846B, SBC846B, BC847B, SBC847B BC848C ($I_C = 2.0\text{ mA}, V_{CE} = 5.0\text{ V}$) BC846B, SBC846B, BC847B, SBC847B BC848C | h_{FE} | - - 200 420 | 150 270 290 520 | - - 475 800 | - |
| Collector - Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$) ($I_C = 100\text{ mA}, I_B = 5.0\text{ mA}$) | $V_{CE(sat)}$ | - - | - - | 0.25 0.6 | V |
| Base - Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$) ($I_C = 100\text{ mA}, I_B = 5.0\text{ mA}$) | $V_{BE(sat)}$ | - - | 0.7 0.9 | - - | V |
| Base - Emitter Voltage ($I_C = 2.0\text{ mA}, V_{CE} = 5.0\text{ V}$) ($I_C = 10\text{ mA}, V_{CE} = 5.0\text{ V}$) | $V_{BE(on)}$ | 580 - | 660 - | 700 770 | mV |

SMALL-SIGNAL CHARACTERISTICS

| | | | | | |
|--|-----------|-----|---|-----|-----|
| Current - Gain - Bandwidth Product ($I_C = 10\text{ mA}, V_{CE} = 5.0\text{ Vdc}, f = 100\text{ MHz}$) | f_T | 100 | - | - | MHz |
| Output Capacitance ($V_{CB} = 10\text{ V}, f = 1.0\text{ MHz}$) | C_{obo} | - | - | 4.5 | pF |
| Noise Figure ($I_C = 0.2\text{ mA}, V_{CE} = 5.0\text{ Vdc}, R_S = 2.0\text{ k}\Omega, f = 1.0\text{ kHz}, BW = 200\text{ Hz}$) | NF | - | - | 10 | dB |

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

ELECTRICAL CHARACTERISTICS (PNP) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|---------------|----------------------|-------------|-------------|---------------------|
| OFF CHARACTERISTICS | | | | | |
| Collector – Emitter Breakdown Voltage ($I_C = -10\text{ mA}$) BC846, SBC846 Series BC847, SBC847 Series BC848 Series | $V_{(BR)CEO}$ | -65 -45 -30 | - - - | - - - | V |
| Collector – Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$) BC846, SBC846 Series BC847, SBC847 Series BC848 Series | $V_{(BR)CES}$ | -80 -50 -30 | - - - | - - - | V |
| Collector – Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$) BC846, SBC846 Series BC847, SBC847 Series BC848 Series | $V_{(BR)CBO}$ | -80 -50 -30 | - - - | - - - | V |
| Emitter – Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$) BC846, SBC846 Series BC847, SBC847 Series BC848 Series | $V_{(BR)EBO}$ | -5.0 -5.0 -5.0 | - - - | - - - | V |
| Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$) | I_{CBO} | - - | - - | -15 -4.0 | nA μA |

ON CHARACTERISTICS

| | | | | | |
|---|---------------|----------------------|--------------------------|----------------------|---|
| DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$) BC846B, SBC846B, BC847B, SBC847B BC848C ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) BC846B, SBC846B, BC847B, SBC847B BC848C | h_{FE} | - - 200 420 | 150 270 290 520 | - - 475 800 | - |
| Collector – Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{CE(sat)}$ | - - | - - | -0.3 -0.65 | V |
| Base – Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{BE(sat)}$ | - - | -0.7 -0.9 | - - | V |
| Base – Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$) | $V_{BE(on)}$ | -0.6 - | - - | -0.75 -0.82 | V |

SMALL-SIGNAL CHARACTERISTICS

| | | | | | |
|--|----------|-----|---|-----|-----|
| Current – Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$) | f_T | 100 | - | - | MHz |
| Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$) | C_{ob} | - | - | 4.5 | pF |
| Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$) | NF | - | - | 10 | dB |

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL NPN CHARACTERISTICS – BC846/SBC846

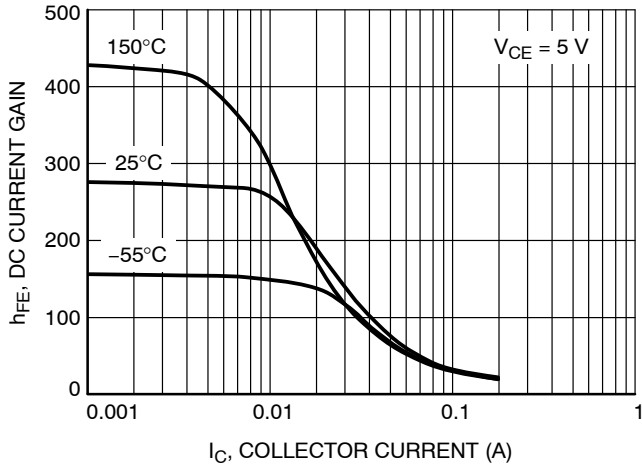


Figure 1. DC Current Gain vs. Collector Current

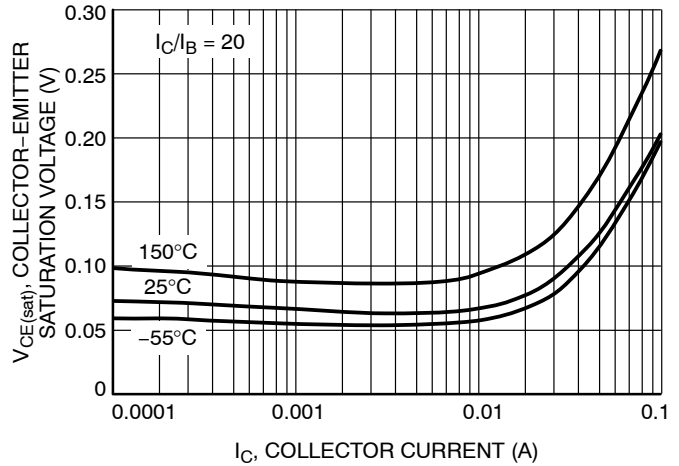


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

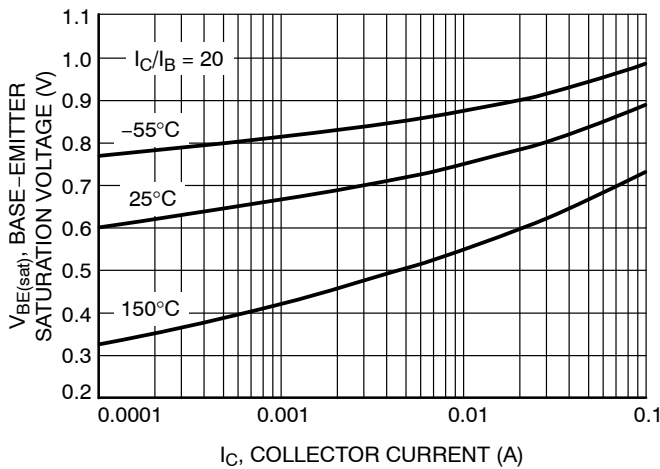


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

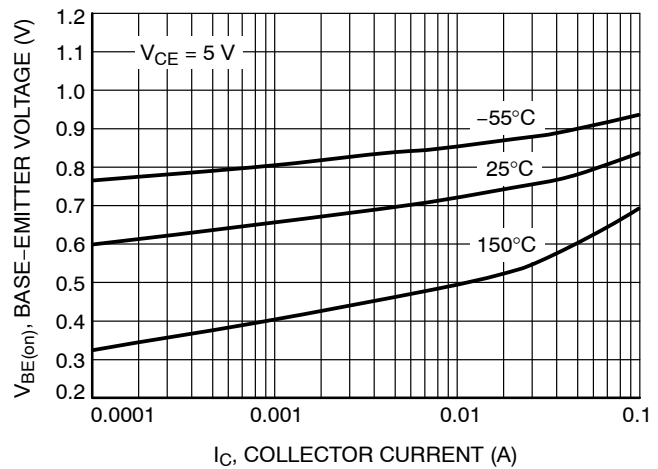


Figure 4. Base Emitter Voltage vs. Collector Current

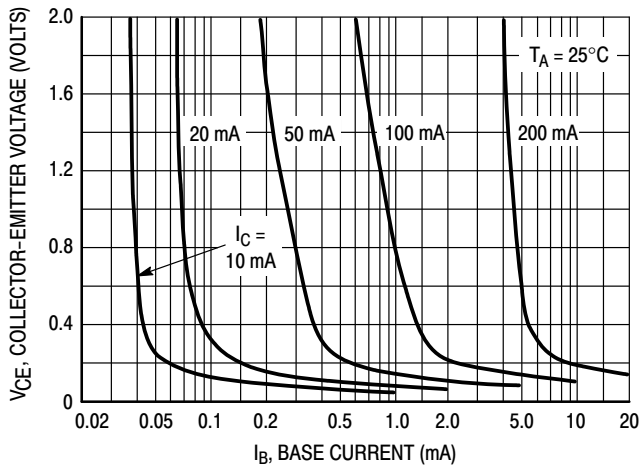


Figure 5. Collector Saturation Region

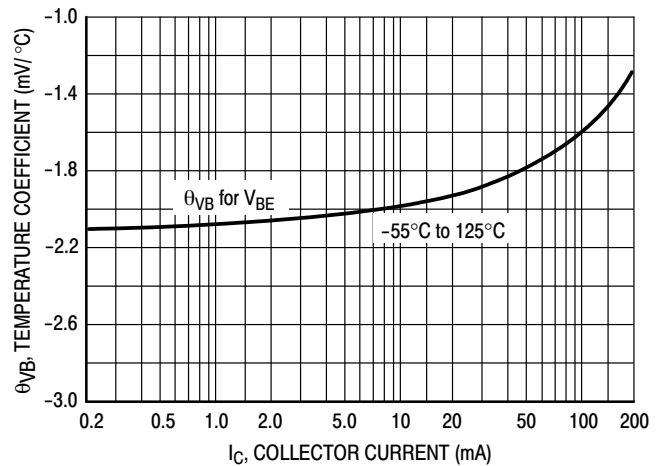


Figure 6. Base-Emitter Temperature Coefficient

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL NPN CHARACTERISTICS – BC846/SBC846

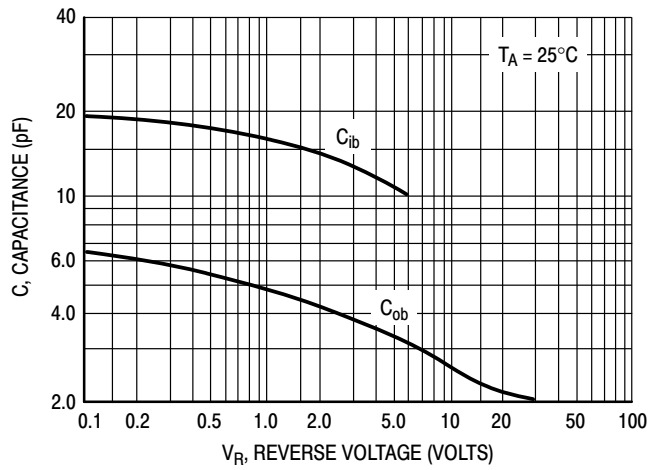


Figure 7. Capacitance

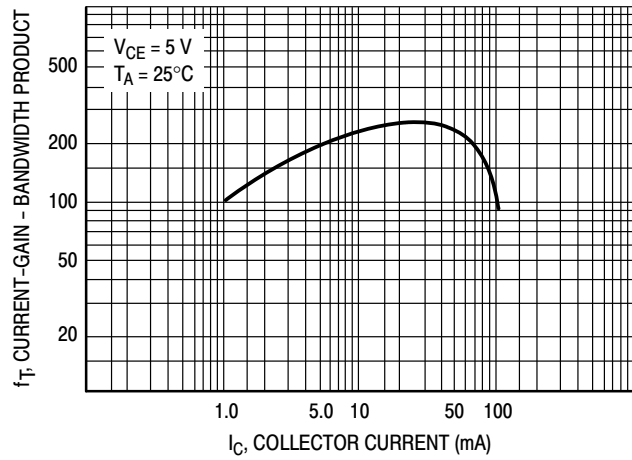


Figure 8. Current-Gain - Bandwidth Product

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL PNP CHARACTERISTICS — BC846/SBC846

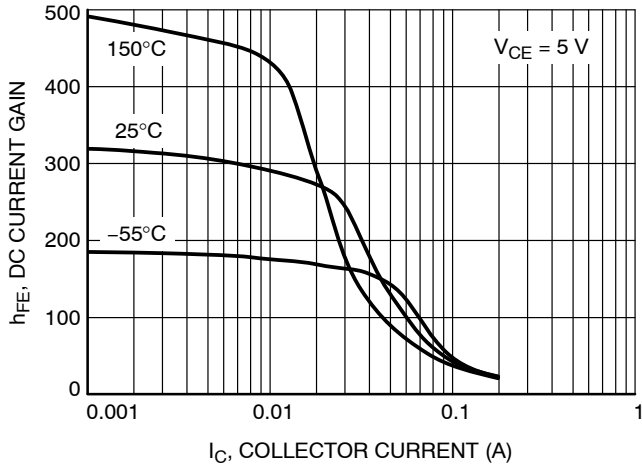


Figure 9. DC Current Gain vs. Collector Current

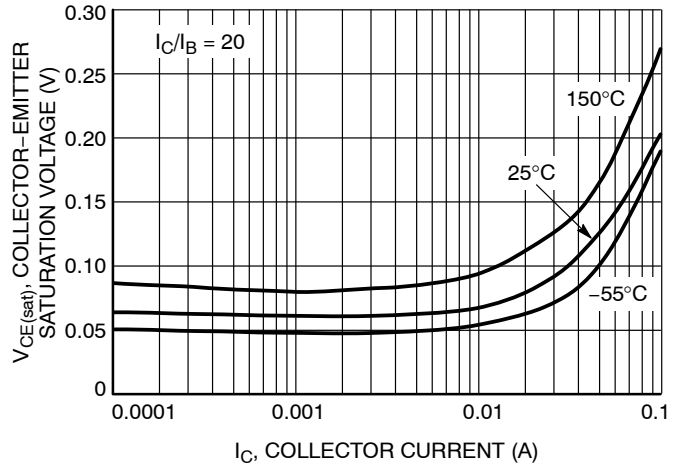


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

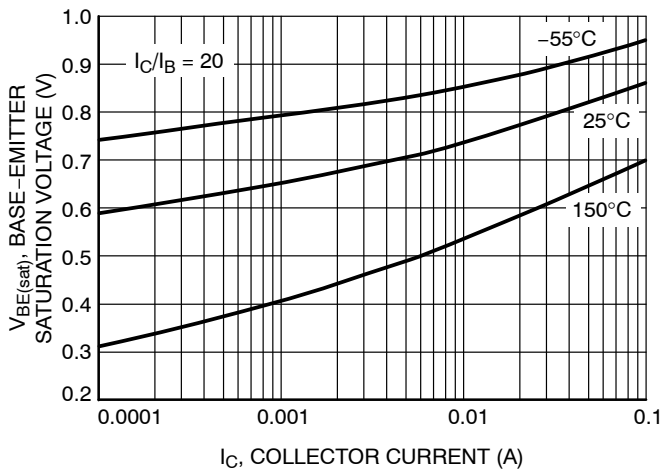


Figure 11. Base Emitter Saturation Voltage vs. Collector Current

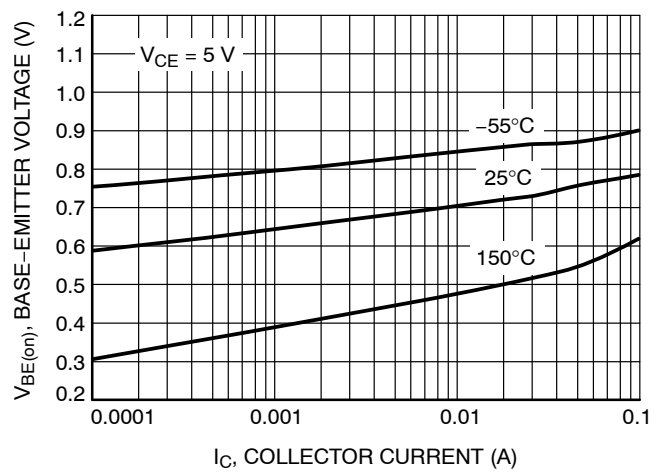


Figure 12. Base Emitter Voltage vs. Collector Current

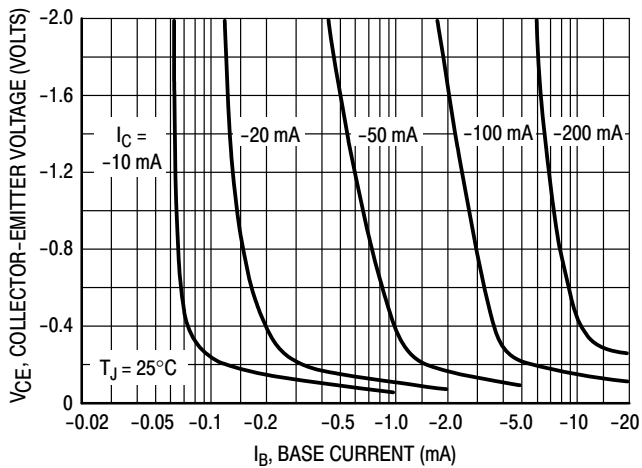


Figure 13. Collector Saturation Region

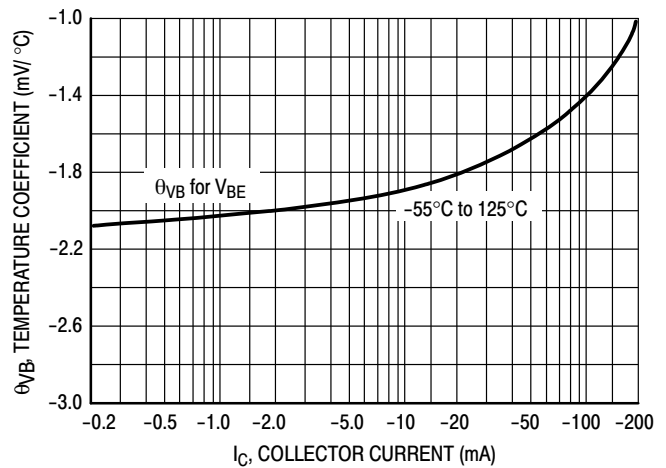


Figure 14. Base-Emitter Temperature Coefficient

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL PNP CHARACTERISTICS — BC846/SBC846

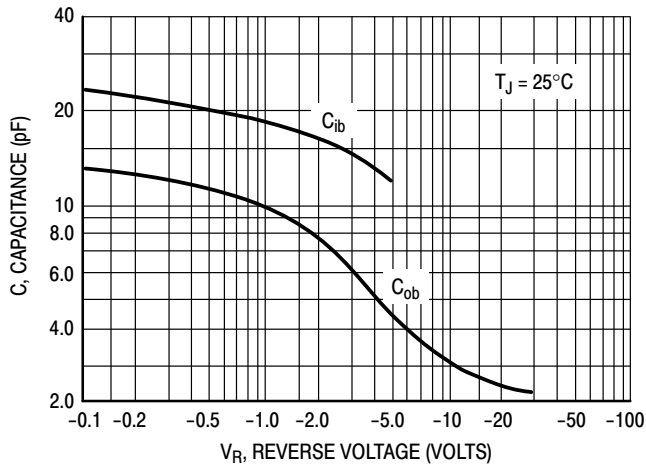


Figure 15. Capacitance

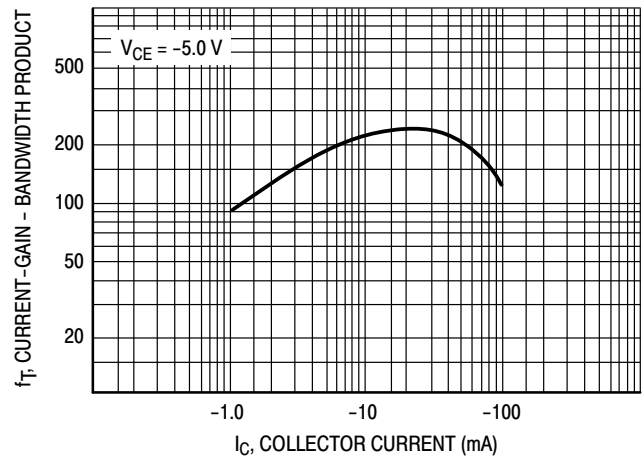


Figure 16. Current-Gain - Bandwidth Product

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL NPN CHARACTERISTICS – BC847/SBC847 SERIES

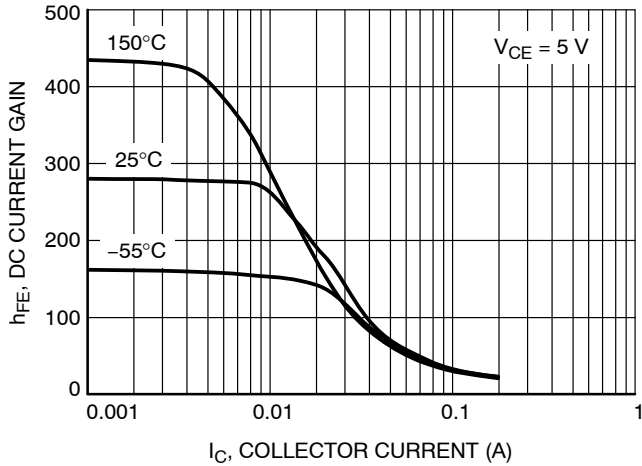


Figure 17. DC Current Gain vs. Collector Current

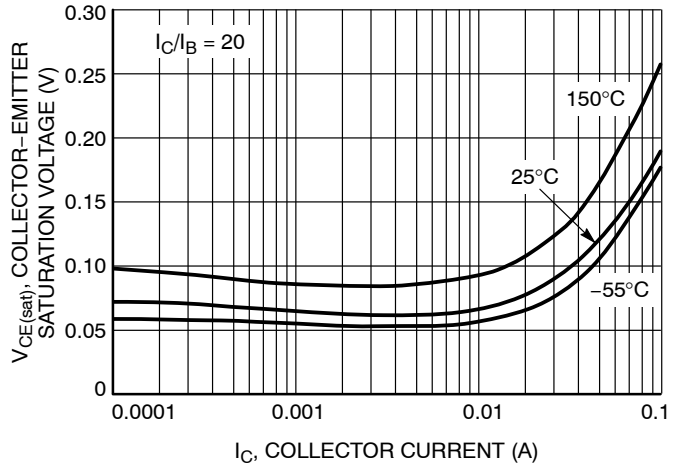


Figure 18. Collector Emitter Saturation Voltage vs. Collector Current

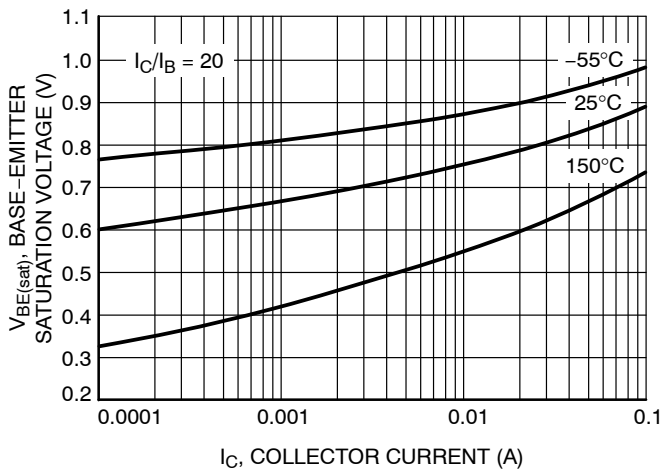


Figure 19. Base Emitter Saturation Voltage vs. Collector Current

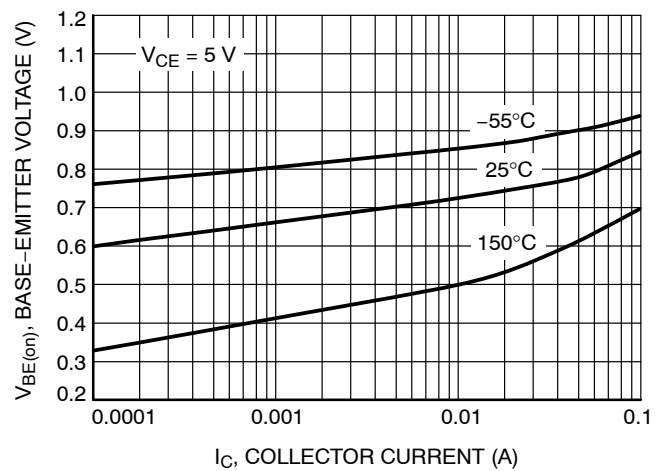


Figure 20. Base Emitter Voltage vs. Collector Current

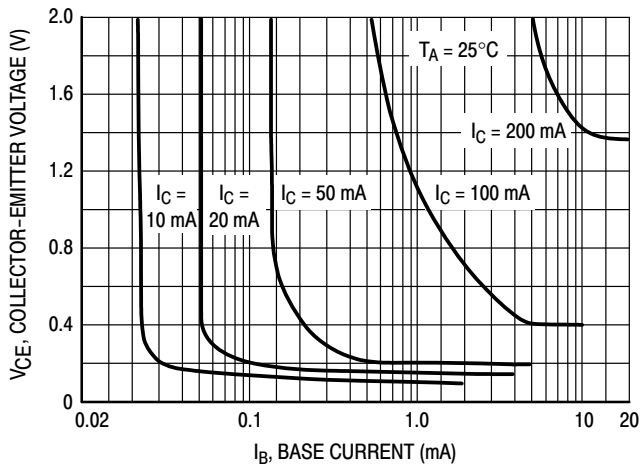


Figure 21. Collector Saturation Region

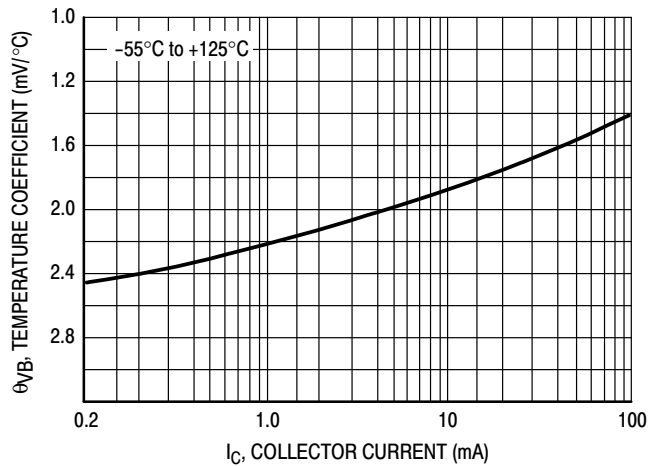


Figure 22. Base-Emitter Temperature Coefficient

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL NPN CHARACTERISTICS – BC847/SBC847 SERIES

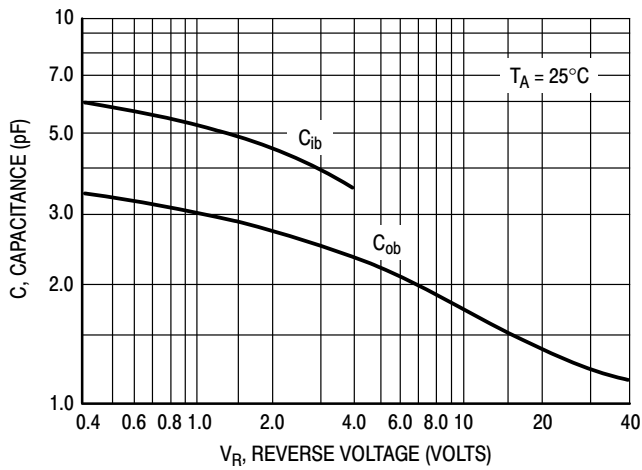


Figure 23. Capacitances

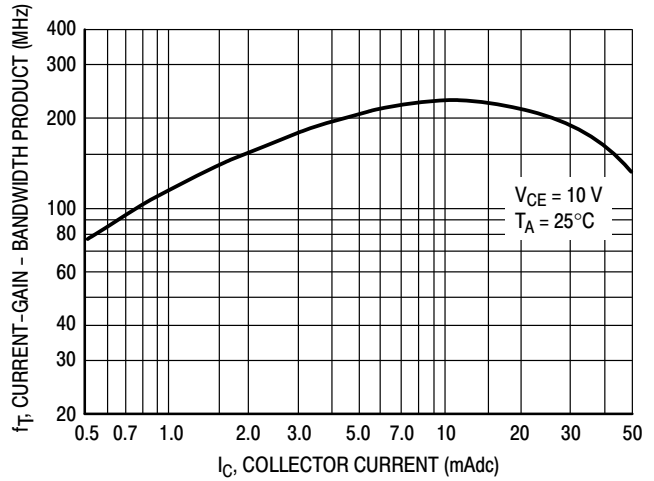


Figure 24. Current-Gain - Bandwidth Product

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL PNP CHARACTERISTICS – BC847/SBC847 SERIES

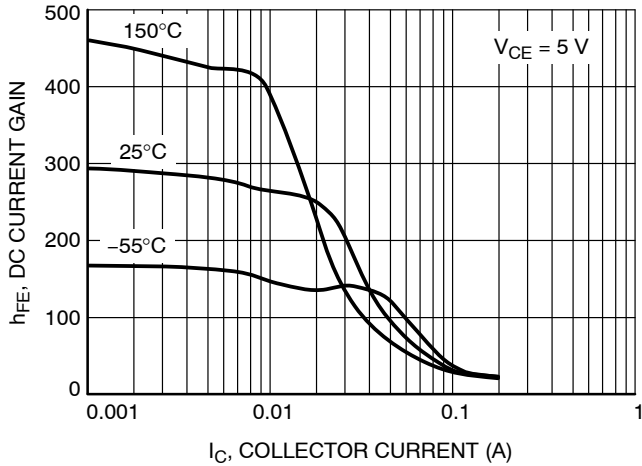


Figure 25. DC Current Gain vs. Collector Current

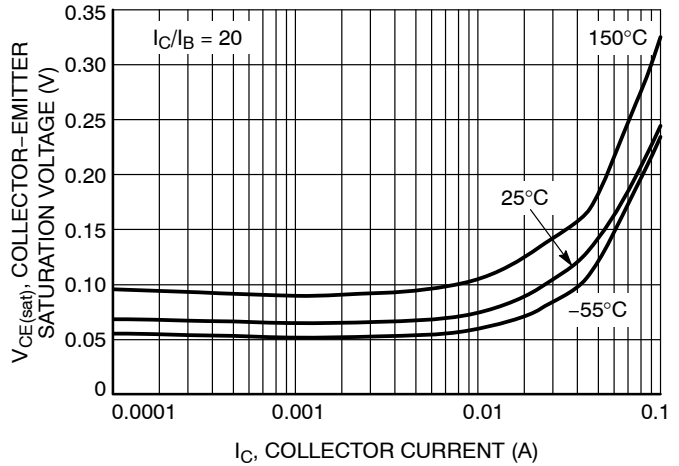


Figure 26. Collector Emitter Saturation Voltage vs. Collector Current

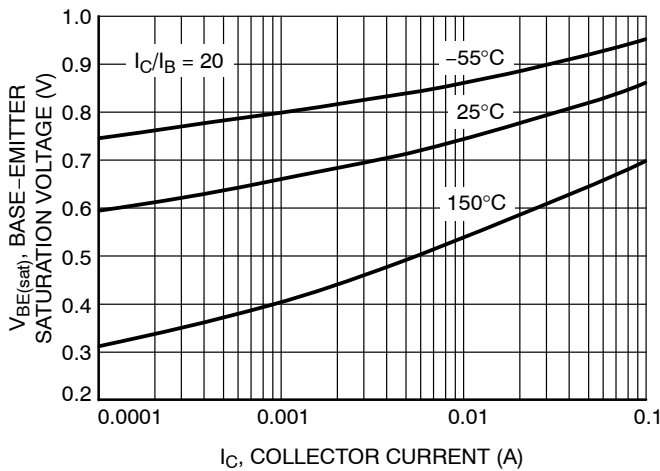


Figure 27. Base Emitter Saturation Voltage vs. Collector Current

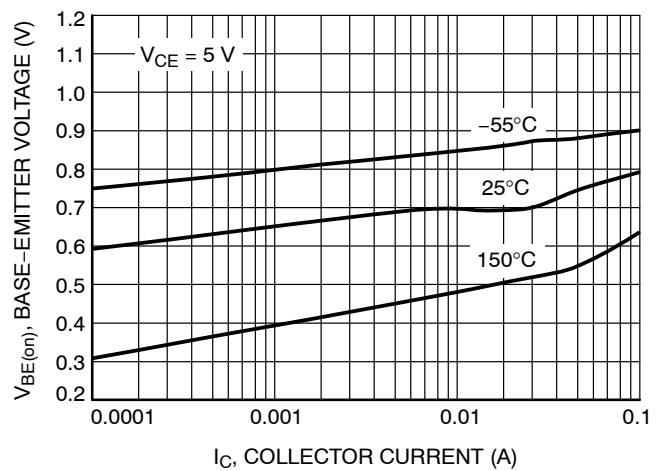


Figure 28. Base Emitter Voltage vs. Collector Current

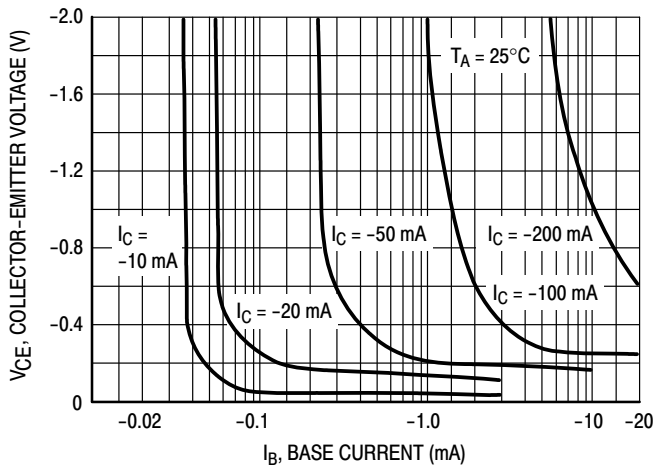


Figure 29. Collector Saturation Region

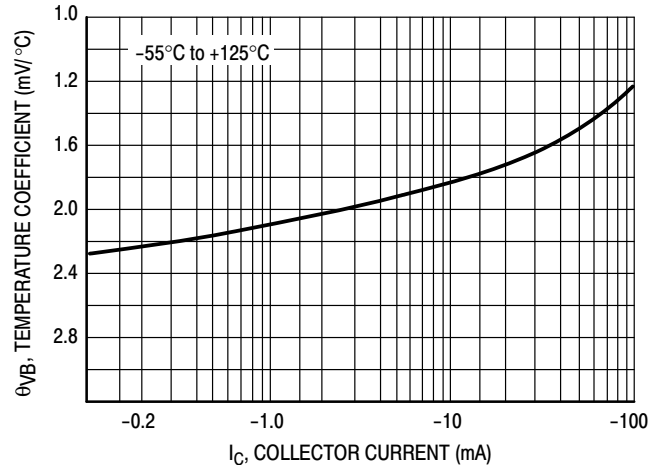


Figure 30. Base-Emitter Temperature Coefficient

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL PNP CHARACTERISTICS – BC847/SBC847 SERIES

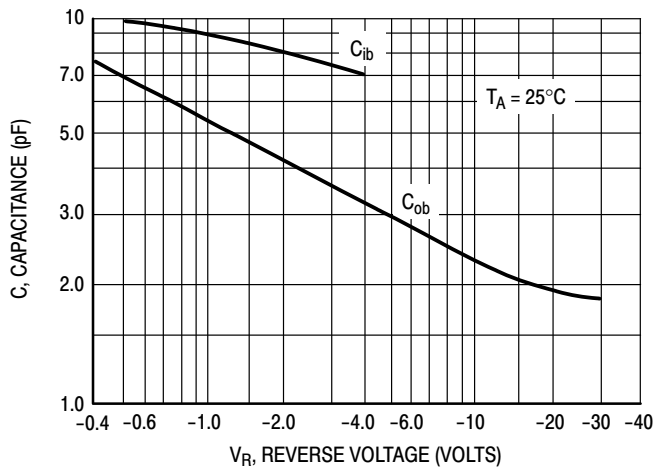


Figure 31. Capacitances

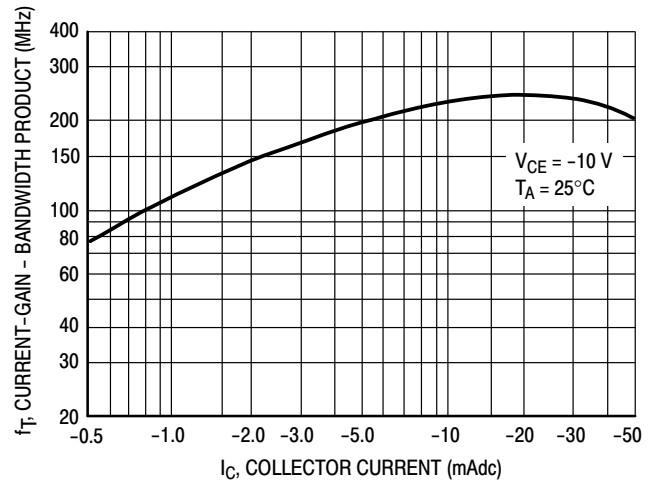


Figure 32. Current-Gain - Bandwidth Product

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL NPN CHARACTERISTICS - BC848 SERIES

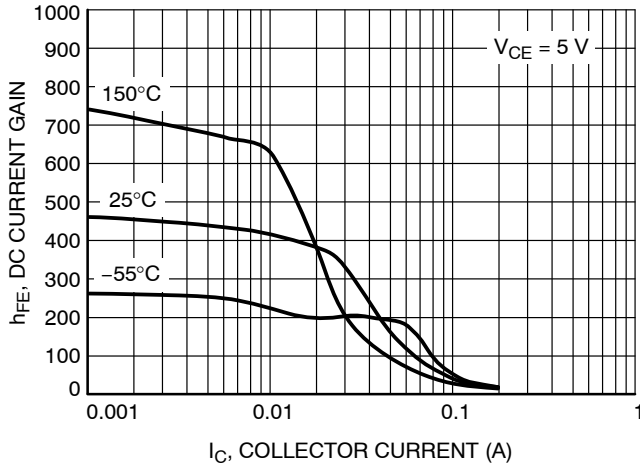


Figure 33. DC Current Gain vs. Collector Current

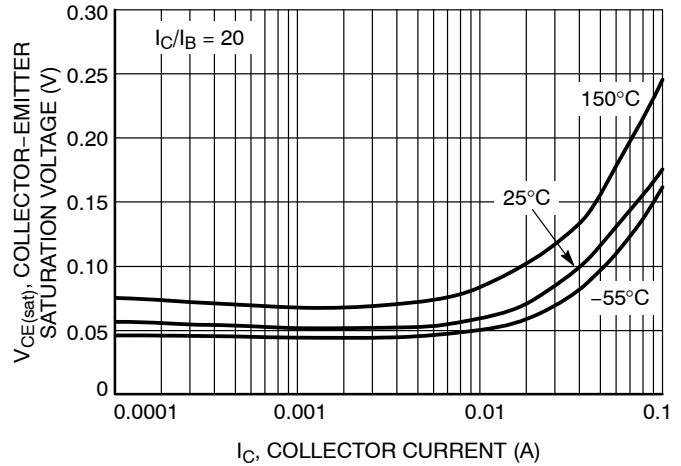


Figure 34. Collector Emitter Saturation Voltage vs. Collector Current

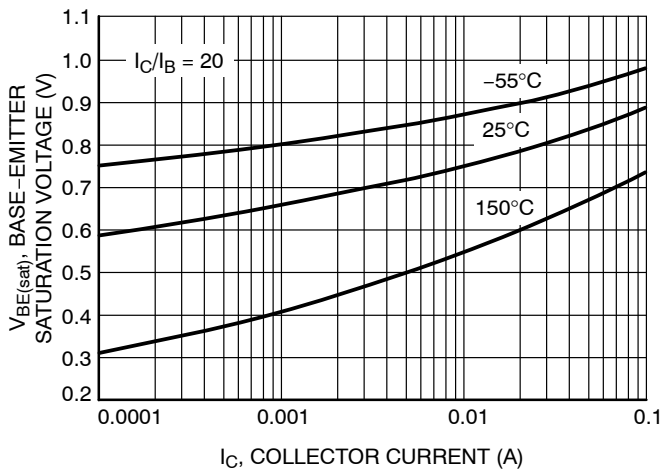


Figure 35. Base Emitter Saturation Voltage vs. Collector Current

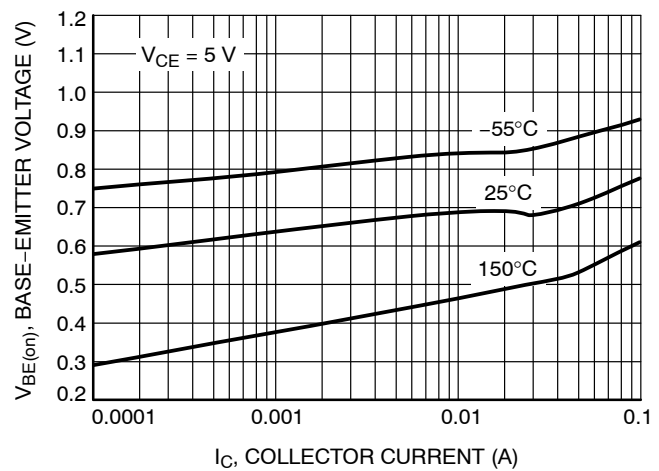


Figure 36. Base Emitter Voltage vs. Collector Current

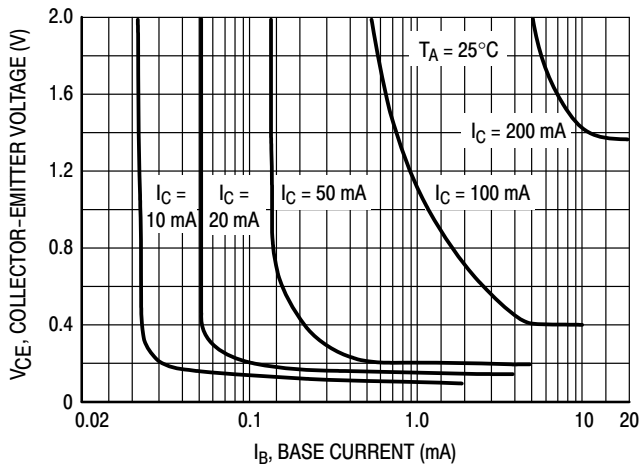


Figure 37. Collector Saturation Region

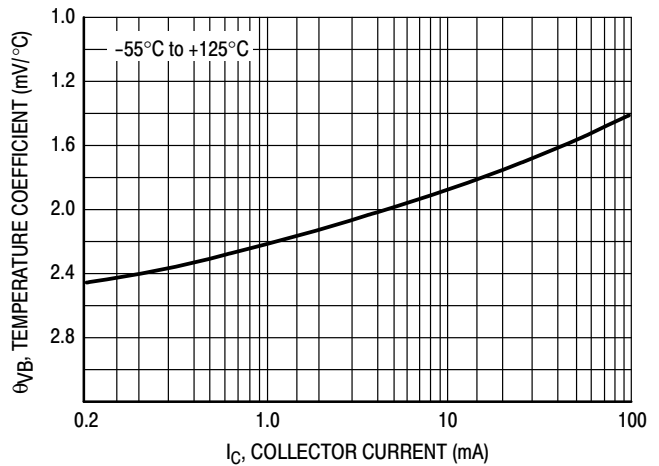


Figure 38. Base-Emitter Temperature Coefficient

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL NPN CHARACTERISTICS – BC848 SERIES

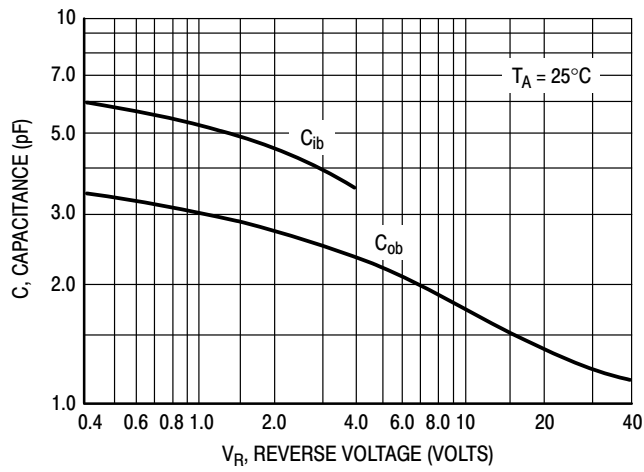


Figure 39. Capacitances

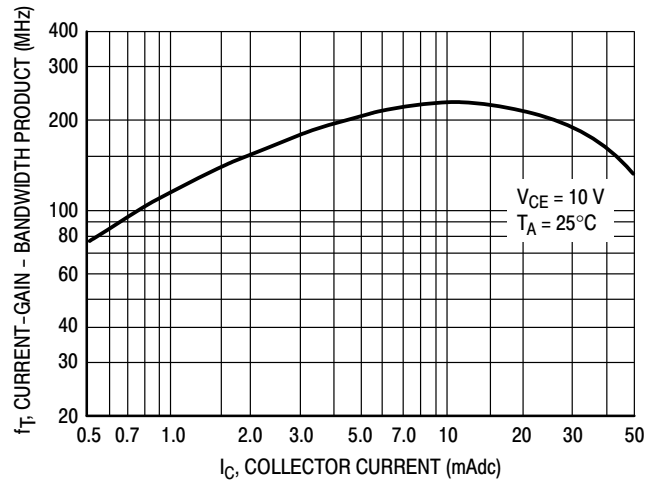


Figure 40. Current-Gain - Bandwidth Product

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL PNP CHARACTERISTICS - BC848 SERIES

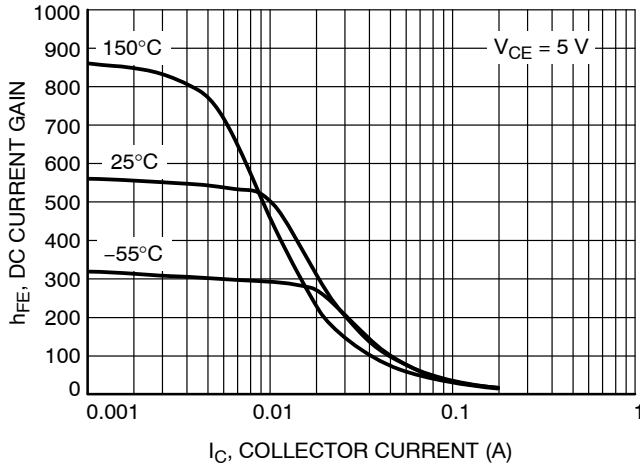


Figure 41. DC Current Gain vs. Collector Current

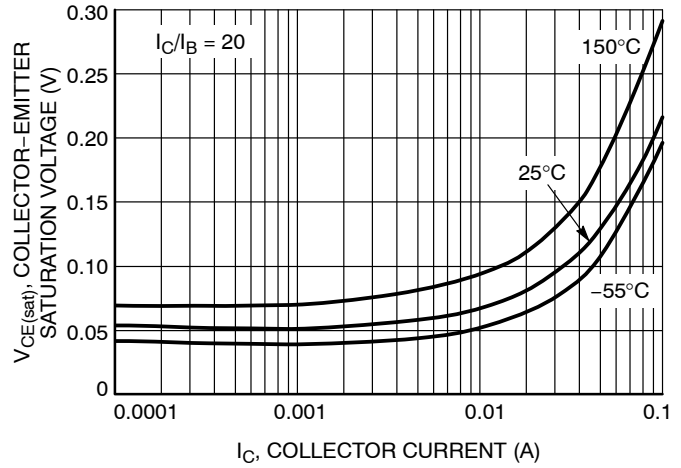


Figure 42. Collector Emitter Saturation Voltage vs. Collector Current

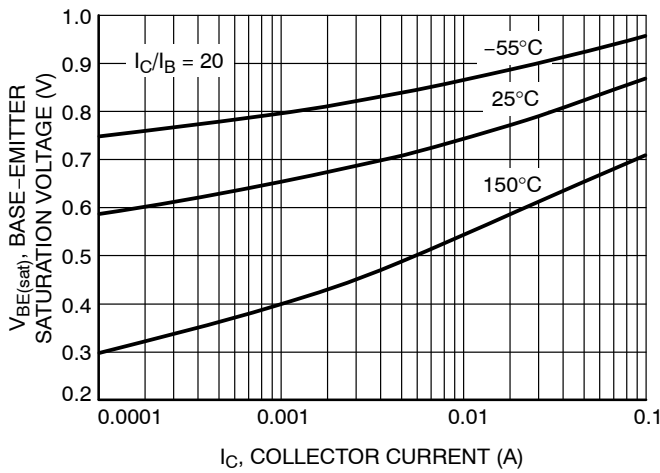


Figure 43. Base Emitter Saturation Voltage vs. Collector Current

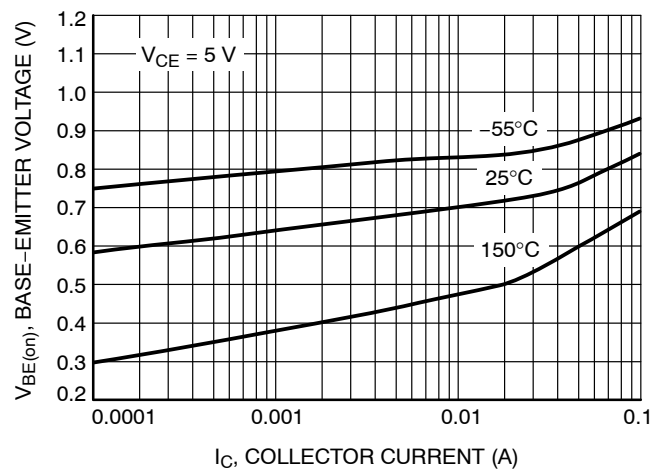


Figure 44. Base Emitter Voltage vs. Collector Current

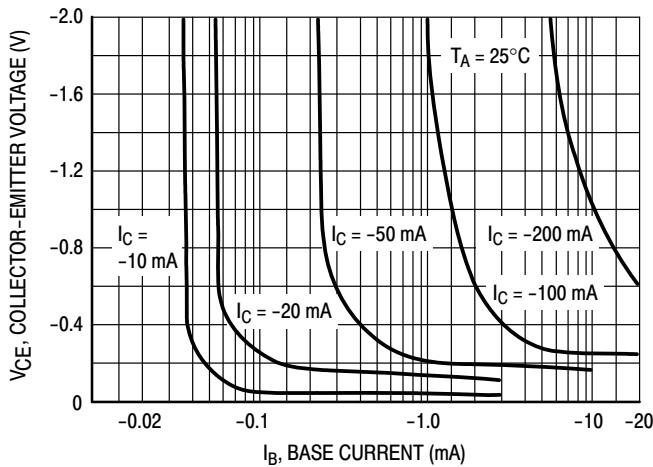


Figure 45. Collector Saturation Region

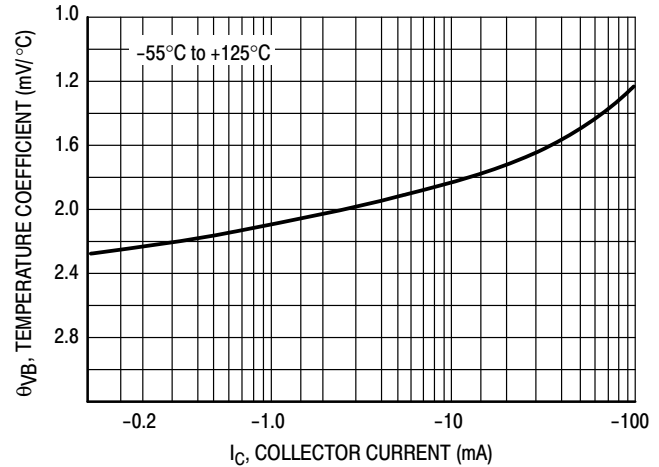


Figure 46. Base-Emitter Temperature Coefficient

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

TYPICAL PNP CHARACTERISTICS – BC848 SERIES

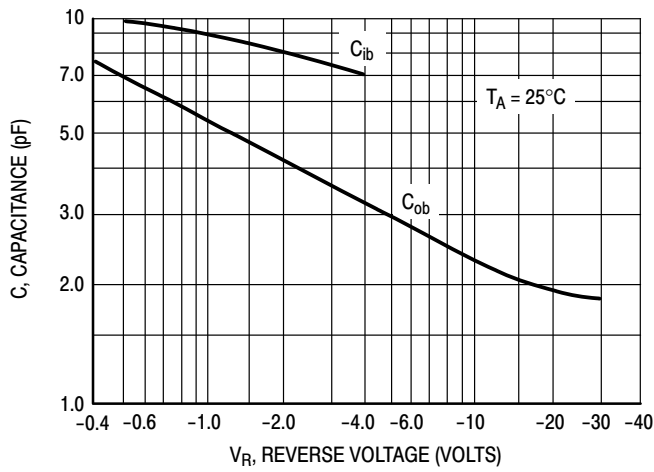


Figure 47. Capacitances

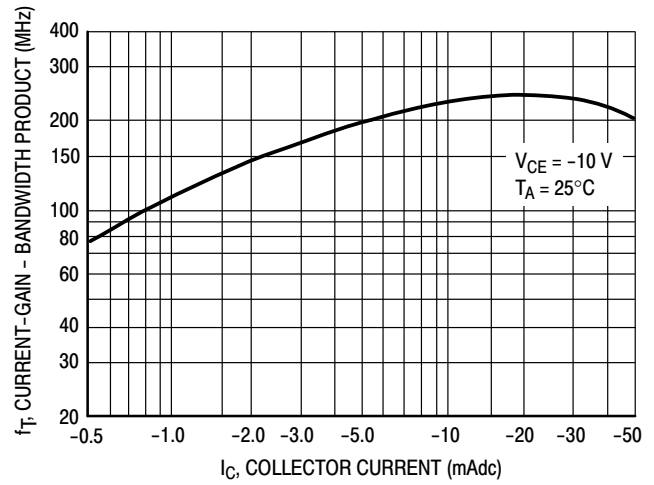


Figure 48. Current-Gain - Bandwidth Product

**BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G,
SBC847BPDW1T1G Series, BC848CPDW1T1G**

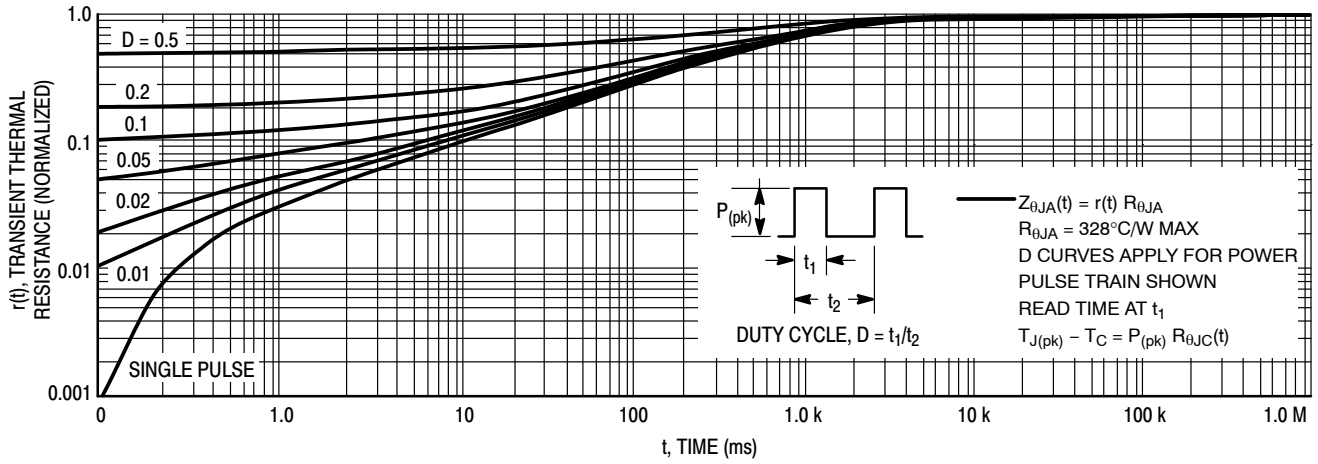


Figure 49. Thermal Response

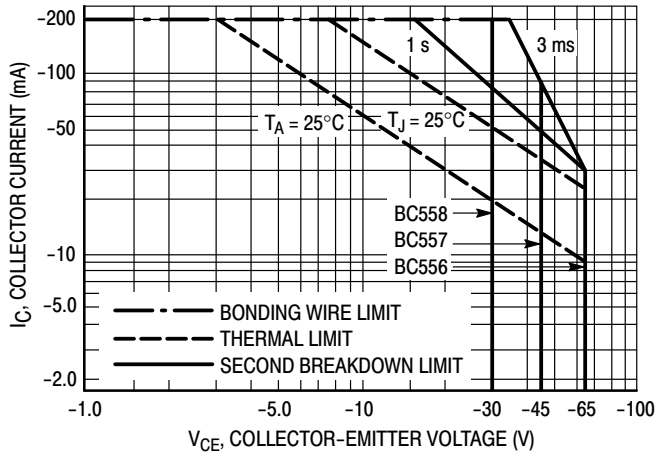


Figure 50. Active Region Safe Operating Area

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 50 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 49. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

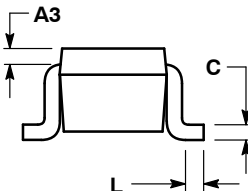
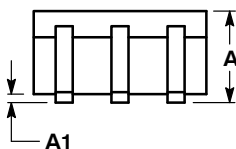
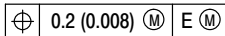
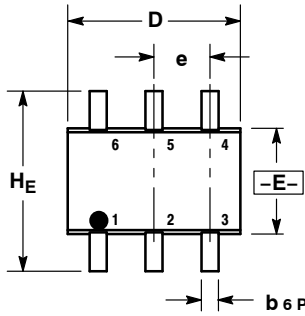
BC846BPDW1T1G, SBC846BPDW1T1G, BC847BPDW1T1G, SBC847BPDW1T1G Series, BC848CPDW1T1G

PACKAGE DIMENSIONS

SC-88/SOT-363/SC70-6

CASE 419B-02

ISSUE W



NOTES:

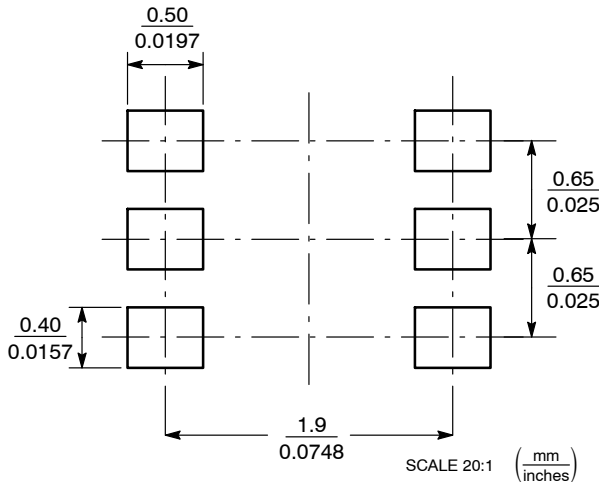
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.80 | 0.95 | 1.10 | 0.031 | 0.037 | 0.043 |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |
| A3 | 0.20 REF | | | 0.008 REF | | |
| b | 0.10 | 0.21 | 0.30 | 0.004 | 0.008 | 0.012 |
| C | 0.10 | 0.14 | 0.25 | 0.004 | 0.005 | 0.010 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| HE | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |

STYLE 1:

- PIN 1. EMITTER 2
- BASE 2
- COLLECTOR 1
- EMITTER 1
- BASE 1
- COLLECTOR 2

SOLDERING FOOTPRINT*



SC-88/SC70-6/SOT-363

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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